

Super Light Sensitivity Feature

<http://www.aiplab.com/>
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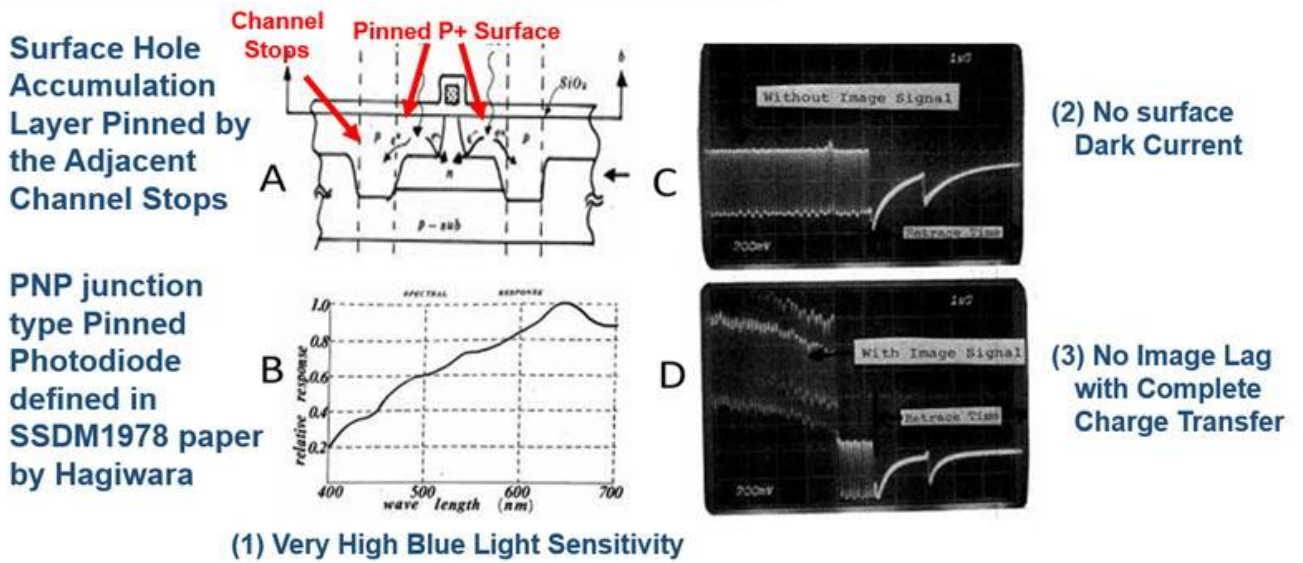


Fig 3: Features of P+PN junction type Pinned Photodiode

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Slide 15

The figure 3 shows important features of the PNP junction type Pinned Photodiode developed by Hagiwara in 1978 .

The surface P layer must be exposed to the silicon oxide, and must be pinned always to the substrate potential by the adjacent channel stops.